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## INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

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Application Number

PCT/DE98/03794

Applicant(s)

Erzgraeber et al.

Filing Date

21 June 2000

Group Art Unit

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.S.	A	4,910,165	3/1990	Lee et al.	437	90	
A.S.	B	5,548,150	8/1996	Omura et al.	257	349	
A.S.	C	5,736,749	4/1998	Xie	257	3	

## FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
A.S.	a	09082968	3/1997	Japan	H01L	29/786	Öä	✓

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

A.S.	aa	IEEE Microwave and Guided Wave Letters, Vol. 7, No. 8, August 1997: Nam et al. High-Performance Planar Inductor on Thick Oxidized Porous Silicon (OPS) Substrate
A.S.	bb	Barla et al.: SOI Technology Using Buried Layers of Oxidized Porous Si; IEEE Circuits and Devices Magazine, 1 November 1987, Pages 11-15

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.